MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS VOLUME 184

Degradation Mechanisms in III-V Compound Semiconductor Devices and Structures

Symposium held April 17-18, 1990, San Francisco, California, U.S.A.

EDITORS:

V. Swaminathan
AT&T Bell Laboratories, Breinigsville, Pennsylvania, U.S.A.

S.J. Pearton
AT&T Bell Laboratories, Murray Hill, New Jersey, U.S.A.

M.O. Manasreh
Electronic Technology Laboratory, Wright Patterson Air Force Base, Dayton, Ohio, U.S.A.

MATERIALS RESEARCH SOCIETY
Pittsburgh, Pennsylvania

CAMBRIDGE UNIVERSITY PRESS
Cambridge, New York, Melbourne, Madrid, Cape Town,
Singapore, São Paulo, Delhi, Mexico City

Cambridge University Press
32 Avenue of the Americas, New York NY 10013-2473, USA

Published in the United States of America by Cambridge University Press, New York

www.cambridge.org
Information on this title: www.cambridge.org/9781107410145

Materials Research Society
506 Keystone Drive, Warrendale, PA 15086
http://www.mrs.org

First published 1990
First paperback edition 2012

Single article reprints from this publication are available through
University Microfilms Inc., 300 North Zeeb Road, Ann Arbor, MI 48106

CODEN: MRSPDH

ISBN 978-1-107-41014-5 Paperback

This work was supported in part by the U.S. Army Research Office under Grant
Number DAAL03-90-G-0087. The views, opinions, and/or findings contained in this
report are those of the authors and should not be construed as an official Department of
the Army position, policy, or decision unless so designated by other documentation.

This work was supported by the Air Force Office of Scientific Research, Air Force
Systems Command, USAF, under Grant Number AFOSR 90-0260.